

REMARKS

The Official Action mailed August 6, 2002 has been received and its contents carefully noted. This response is filed within three months of the mailing date of the Official Action and therefore is believed to be timely without extension of time.

Applicants note with appreciation the consideration of the Information Disclosure Statements filed on October 31, 2000; July 5, 2001; January 30, 2002; and February 5, 2002. A further IDS is submitted herewith and careful review and consideration of this IDS is requested.

Claims 1-34 were pending in the present application. Claims 4-34 have been canceled, claim 1 has been amended and new claims 35-51 have been added to recite additional protection to which Applicants are entitled. The features of new claims 35-51 are supported by the Fourth Embodiment and the Sixth Embodiment of the present application (Please see page 24, line 1 to page 29, line 4 and page 30, line 7 to page 33, line 15). Claims 1-3 and 35-51 are now pending in the present application, of which claims 1 and 35-45 are independent. For the reasons set forth in detail below, all claims are believed to be in condition for allowance and favorable reconsideration is requested.

Paragraph 3 of the Official Action rejects claims 1-13, 15-17, 19 and 26-34 as anticipated by U.S. Patent 5,728,259 to Suzawa. It is well established that "a claim is anticipated only if each and every element as set forth in the claim is found, either expressly or inherently described, in a single prior art reference." *Verdegaal Bros. v. Union Oil Co. of California*, 814 F.2d 628, 631, 2 USPQ2d 1051, 1053 (Fed. Cir. 1987).

Claims 2-13, 15-17, 19 and 26-34 have been canceled rendering the rejection of these claims moot. Furthermore, claim 1 has been amended to recite that a first gate insulating film is formed over the semiconductor island wherein the first gate insulating film comprises silicon oxide, a second gate insulating film is formed over the first gate insulating film wherein the second gate insulating film comprises silicon oxide nitride, a gate electrode is formed over the semiconductor island with the first gate insulating film and the second gate insulating film therebetween and at least a source region and a drain region are formed in the semiconductor island (Please see the Sixth Embodiment discussed on page 30, line 7 to page 33, line 15 of the present specification). It is

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respectfully submitted that Suzawa fails to disclose these features as recited in claim 1 and that claim 1 is therefore not anticipated thereby. Reconsideration is requested.

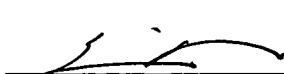
Paragraph 6 of the Official Action rejects claims 14, 18 and 20-25 as obvious based on the combination of Suzawa and U.S. Patent 5,550,070 to Funai. Paragraph 7 of the Official Action of the Official Action rejects claim 24 as obvious based on the combination of Suzawa, Funai and Gandhi, VLSI Fabrication Principles, John Wiley and Sons, p. 388, 1983. In response, Applicants have canceled these claims and therefore this rejection is believed to be moot.

Paragraph 9 of the Official Action rejects claims 1-2, 4, 7, 11, 15, 20 and 26-28 under the judicial doctrine of obviousness-type double patenting over claims 5 and 6 of U.S. Patent 6,180,439. In response, the amendment to claim 1 are believed to patentably distinguish the claim over claims 5 and 6 of the '439 patent and reconsideration of the double patenting rejection in view of these amendments is requested. The remaining claims have been canceled rendering the rejection moot. Similarly, the rejections set forth in paragraphs 10-15 are believed to be moot in that the rejected claims have been canceled herewith.

Finally, new claims 35-51 are believed to be patentably distinguished from the prior art of record for the same reasons discussed above in connection with claim 1 and favorable consideration of these claims is requested.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,

  
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**VERSION WITH MARKINGS TO SHOW CHANGES MADE**

**IN THE CLAIMS:**

Please cancel claims 4-34 and amend claim 1 as follows:

1. (Amended) A method for manufacturing a semiconductor device comprising [the steps of]:

forming a semiconductor film on an insulating surface; [and]

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface;

forming a first gate insulating film over the semiconductor island wherein the first gate insulating film comprises silicon oxide;

forming a second gate insulating film over the first gate insulating film wherein the second gate insulating film comprises silicon oxide nitride;

forming a gate electrode over the semiconductor island with the first gate insulating film and the second gate insulating film therebetween; and

forming at least a source region and a drain region in the semiconductor island,

wherein irradiation of laser light is performed after forming said semiconductor film.

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